

Photocouplers Infrared LED & Photo IC

# **TLP5212**

#### 1. Applications

- IGBT Gate Drivers
- MOSFET Gate Drivers
- Industrial Inverters
- AC Servos
- Photovoltaic (PV) Power Conditioning Systems
- Air Conditioner Inverters

#### 2. General

The TLP5212 is a highly integrated 2.5 A output current IGBT gate drive photocoupler housed in a long creepage and clearance SO16L package.

The TLP5212, a smart gate driver photocoupler, includes functions of IGBT desaturation detection, isolated fault status feedback, soft gate turn-off, active Miller cramping and under voltage lockout (UVLO).

The TLP5212 consists two infrared light-emitting diodes (LEDs) and two high-gain and high-speed Light-receiving IC chips. They realize the control of output current and the feedback function of the fault signal with electrical isolation between a primary side and secondary side.

#### 3. Features

(1) Peak output current  $: \pm 2.5 \text{ A (max)}$ (2) Guaranteed performance over temperature : - 40 to 110 ℃ (3) Power supply voltage : 15 V to 30 V (4) Threshold input current : 6 mA (max) (5) Supply current : 5 mA (max) (6) Propagation delay time : 250 ns (max) (7) DESAT leading edge blanking time : 1.27 µs (typ) (8) Common-mode transient immunity  $\pm 25 \text{ kV/}\mu\text{s} \text{ (min)}$ (9) Isolation voltage : 5000 Vrms (min)

(10) Safety standards

UL approved : UL1577, File No. E67349

cUL approved : CSA Component Acceptance Service No.5A File No. E67349

VDE approved : EN60747-5-5 (Note 1)

CQC approved : GB4943.1, GB8898 Japan Factory



仅适用干海拔 2000m 以下地区安全使用

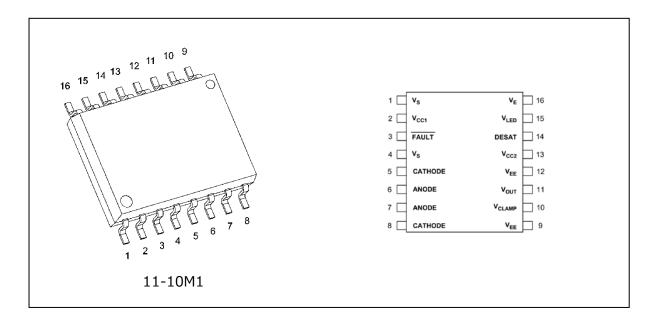
Note 1: When a VDE approved type is needed, please designate the Option (D4).

Start of commercial production

2022-04



## 4. Packaging and Pin Assignment

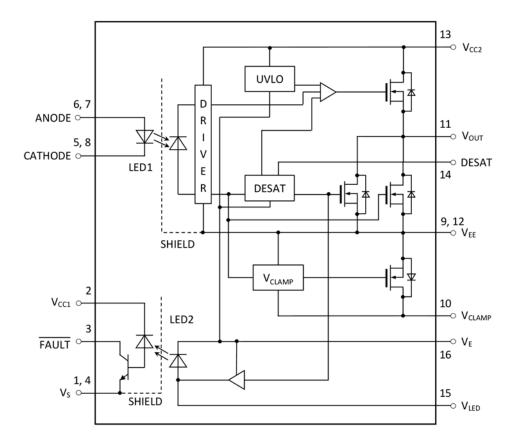


### 4.1. Pin Description

Pin No.	Symbol	Description	
1	Vs	Input side ground	
2	Vcc1	Positive input supply voltage. (2.7 V to 5.5 V)	
3	FAULT	Fault output	
4	Vs	Input side ground	
5	CATHODE	Input side LED Cathode	
6	ANODE	Input side LED Anode	
7	ANODE	Input side LED Anode	
8	CATHODE	Input side LED Cathode	
9	VEE	Negative output supply voltage	
10	VCLAMP	Miller current clamp	
11	Vout	Gate drive voltage output	
12	VEE	Negative output supply voltage	
13	Vcc2	Positive output supply voltage	
14	DESAT	Desaturation voltage input	
15	VLED	Not connect, for testing only	
16	VE	Common (IGBT emitter) output supply voltage.	



### 5. Internal Circuit (Note)



Note : Bypass capacitors (1  $\mu$ F) must be connected between pin 13 ( $V_{CC2}$ ) and 16 ( $V_E$ ) to stabilize the operation of the high gain linear amplifier. When  $V_E - V_{EE} > 0$  V (with negative gate drive), another bypass capacitor (1  $\mu$ F) must be connected between pin 9 or 12 ( $V_{EE}$ ) and 16 ( $V_E$ ). Failure to provide the bypassing may impair the switching property. The total lead length between each capacitor and the coupler should not exceed 1 cm.

### 6. Principle of Operation

#### 6.1. Truth Table

Input Current I <sub>F</sub>	Under Voltage Lock Out UVLO ( V <sub>CC2</sub> - V <sub>E</sub> )	Over current protection DESAT ( Pin14 input )	Feedback function FAULT ( Pin3 output )	IGBT Gate voltage V <sub>OUT</sub>
ON	Active ( < V <sub>UVLO</sub> -)	Not Active	High	Low
ON	Not Active ( > V <sub>UVLO</sub> <sup>+</sup> )	Active (with DESAT fault)	Low (FAULT)	Low
ON	Not Active ( > V <sub>UVLO</sub> <sup>+</sup> )	Active (no DESAT fault)	High	High
OFF	Active ( < V <sub>UVLO</sub> -)	Not Active	High	Low
OFF	Not Active ( $> V_{UVLO}^+$ )	Not Active	High	Low

#### 6.2. Mechanical Parameters

Characteristics	Dimensions	Unit
Creepage distances	8.0 (min)	
Clearance distances	6.0 (11111)	mm
Internal isolation thickness	0.4 (min)	



### 7. Absolute Maximum Ratings (Note) (Unless otherwise specified, $Ta = 25 \text{ }^{\circ}\text{C}$ )

	Characte	ristics	Symbol	Note	RATING	Unit
	LED Input forward current		$I_{F}$		25	mA
	LED Input forward current de	erating (Ta ≥ 90°C)	$\Delta I_{\text{F}}/\Delta Ta$		-0.65	mA/°C
	Peak transient input LED forv	vard current	$I_{FPT}$	Note 1	1	Α
LED & Feedback	LED Reverse input voltage		$V_R$		5	٧
(controller	FAULT feedback IC supply vo	ltage	V <sub>CC1</sub>		-0.5 to 7	٧
side)	FAULT feedback output curre	ent	I FAULT		8	mA
	FAULT feedback output volta	ge	V FAULT		-0.5 to V <sub>CC1</sub>	V
	Input LED power dissipation		$P_{D}$		60	mW
	Input LED power dissipation	derating (Ta ≥ 90°C)	Δ P <sub>D</sub> /ΔTa		-1.9	mW/°C
	Peak high-level output current	Ta = −40 to 110 °C	I <sub>OPH</sub>	Note 2 Note 3	-2.5	А
	Peak low-level output current	1a = -40 to 110 °C	$I_{OPL}$		+2.5	А
	Total output side supply volta	age	$(V_{CC2}-V_{EE})$		-0.5 to 35	>
Output	Negative output side supply	voltage	$(V_E-V_{EE})$		-0.5 to 15	>
(gate	Positive output side supply vo	oltage	$(V_{CC2}-V_E)$		-0.5 to 35 - (V <sub>E</sub> -V <sub>EE</sub> )	V
Driver	Output voltage		V <sub>OUT</sub>		V <sub>EE</sub> to V <sub>CC2</sub>	V
side)	Peak power device gate clam	ping sinking current	I <sub>Clamp</sub>		2.5	Α
	Miller clamping pin voltage		$V_{Clamp}$		V <sub>EE</sub> to V <sub>CC2</sub>	٧
	DESAT pin voltage		$V_{DESAT}$		V <sub>E</sub> to V <sub>E</sub> + 10	٧
	Output gate drive IC power of	lissipation	PO	Note 3	600	mW
	P <sub>O</sub> derating	(Ta ≥90°C)	Δ P <sub>O</sub> /ΔTa	Note 3	-13.0	mW/°C
Common	Operating temperature range	2	T <sub>opr</sub>		-40 ~ 110	°C
	Storage temperature range		T <sub>stg</sub>		-55 ~ 125	°C
	Lead soldering temperature (	(10 s)	T <sub>sol</sub>	Note 4	260	°C
	Isolation voltage (AC, 60 s, R	R.H. ≤ 60%)	BV <sub>S</sub>	Note 5	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.)

Note 1: Pulse width  $\leq 1~\mu s$ , 300 pps

Note 2: Exponential waveform. Pulse width  $\leq$  0.28  $\mu$ s, f  $\leq$  25 kHz,  $V_{CC2}$  = 15 to 30 V

Note 3: Mounting on a substrate designated in accordance with JEDEC JESD51-7.

Note 4: For the effective lead soldering area.

Note 5: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pins on the photodetector side are shorted together.



### 8. Recommended Operation Conditions (Note)

Characteristics	Symbol	Note	Min	Max	Unit
Total output side supply voltage	(V <sub>CC2</sub> - V <sub>EE</sub> )	Note 1 Note 2	15	30	V
Negative output side supply voltage	(V <sub>E</sub> - V <sub>EE</sub> )	Note 1 Note 3	0	15	٧
Positive output side supply voltage	(V <sub>CC2</sub> - V <sub>E</sub> )	Note 1 Note 2	15	30 - (V <sub>E</sub> - V <sub>EE</sub> )	V
FAULT feedback IC supply voltage	V <sub>CC1</sub>		2.7	5.5	V
LED Input on-state current	I <sub>F(ON)</sub>	Note 4	7.5	12	mA
LED Input off-state voltage	V <sub>F(OFF)</sub>		0	0.8	V

- Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performances of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.
- Note 1: If the rising slopes of V<sub>CC2</sub> and V<sub>EE</sub> are so steep, the internal circuit operation may not be stable. In that case, please design the slopes to be 0.5 V/µs or less.
- Note 2: 15 V is the recommended minimum operating positive supply voltage ( $V_{CC2}$   $V_E$ ) to ensure adequate margin in excess of the maximum  $V_{UVLO+}$  threshold of 12.5V.
- Note 3: This supply is optional. Required only when negative gate drive is implemented.
- Note 4: The rise and fall times of the input on-current should be less than 500  $\mu$ s.



### 9. Electrical Characteristics (Note)

### (Unless otherwise specified, Ta = - 40 to 110 °C, $V_{CC2}$ - $V_{EE}$ = 15 to 30 V, $V_E$ - $V_{EE}$ = 0 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input forward voltage	V <sub>F</sub>			$I_F = 10$ mA, $Ta = 25$ °C	1.48	1.67	1.93	V
Input reverse current	I <sub>R</sub>			V <sub>R</sub> = 5 V, Ta = 25 ℃	-	_	10	μΑ
Input capacitance (between Pin 7 to 8)	Ct			V = 0 V, f = 1 MHz, Ta = 25 ℃	-	20	-	pF
FAULT low level output	VFAULTL			I FAULT = 1.1 mA, V <sub>CC1</sub> = 5.5 V	_	0.1	0.4	V
voltage	VFAULIL			I FAULT = 1.1 mA, $V_{CC1}$ = 2.7 V	_	0.1	0.4	] '
FAULT high level output	I FAULTH			$V_{\overline{FAULT}} = V_{CC1} = 5.5 \text{ V}, Ta = 25 ^{\circ}\text{C}$	ı	0.02	0.5	μA
current	1 FAULIH			$V_{\overline{FAULT}} = V_{CC1} = 2.7 \text{ V, Ta} = 25 ^{\circ}\text{C}$	_	0.002	0.3	μΑ
High level output current	$I_{OPH}$	Note 1	13.1.1	$V_{OUT} = V_{CC2} - 4 V$	_	-2.9	-2.0	Α
Low level output current	$I_{OPL}$	Note 1	13.1.2	$V_{OUT} = V_{EE} + 2.5 V$	2.0	3.1	_	] ^
Low level output current during fault condition	I <sub>OLF</sub>			V <sub>OUT</sub> - V <sub>EE</sub> = 14 V	90	180	230	mA
High level output voltage	V <sub>OH</sub>		13.1.3	I <sub>OUT</sub> = - 650 μA	V <sub>CC2</sub> - 2.9	V <sub>CC2</sub> - 1.6	-	
Low level output voltage	V <sub>OL</sub>		13.1.4	I <sub>OUT</sub> = 100 mA	_	0.12	0.5	٧
Clamp pin threshold voltage	V <sub>tClamp</sub>			I <sub>CL</sub> = 100 mA	-	2.3	-	
Clamp low level sinking current	I <sub>CL</sub>			$V_{Clamp} = V_{EE} + 2.5 V$	0.35	2.4	-	Α
High level supply current	I <sub>CC2H</sub>		13.1.5	$I_F = 10 \text{ mA}$	_	3.2	5	
Low level supply current	I <sub>CC2L</sub>		13.1.6	$I_F = 0 \text{ mA}$	_	2.5	5	
Blanking capacitor charging current	I <sub>CHG</sub>		13.1.7	I <sub>F</sub> = 10 mA, V <sub>DESAT</sub> = 2 V	-0.33	-0.26	-0.13	mA
Blanking capacitor discharging current	I <sub>DSCHG</sub>		13.1.8	V <sub>DESAT</sub> = 7 V	10	28.5	-	
DESAT threshold voltage	V <sub>DESAT</sub>			$I_F = 10$ mA, $I_{DESAT} > 0$	6.0	6.6	7.5	
LIVI O through and violence	V <sub>UVLO</sub> <sup>+</sup>		13.1.9	$I_F = 10 \text{ mA}, V_{OUT} > 5 \text{ V}$	10.5	11.4	12.5	V
UVLO threshold voltage	V <sub>UVLO</sub> -		13.1.9	$I_F = 10$ mA, $V_{OUT} < 5$ V	9.2	10.0	11.1	]
UVLO hysteresis	UVLO <sub>HYS</sub>			(V <sub>UVLO+</sub> - V <sub>UVLO-</sub> )	0.4	1.4	_	
Threshold input current (L/H)	I <sub>FLH</sub>		13.1.10	V <sub>CC2</sub> = 30 V, V <sub>OUT</sub> > 5 V	-	0.96	6	mA
Threshold input voltage (H/L)	V <sub>FHL</sub>			V <sub>CC2</sub> = 30 V, V <sub>OUT</sub> < 5 V	0.8	-	-	V

Note : All typical values are at  $T_a=25~$   $^{\circ}$ C. Note 1:  $I_O$  application time  $\leq 10~$   $\mu s$ , single pulse

### 10. Isolation Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Note	Test conditions	Min	Тур.	Max	Unit
Total capacitance (input to output)	CS	Note 1	V <sub>S</sub> = 0 V, f = 1 MHz	_	1.0	-	pF
Isolation resistance	$R_S$	Note 1	V <sub>S</sub> = 500 V, R.H. ≤ 60 %	10 <sup>12</sup>	10 <sup>14</sup>	-	Ω
Isolation voltage	BV <sub>S</sub>	Note 1	AC, 60 s	5000	_	1	Vrms

Note 1: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pin on the Output side are shorted together.



#### 11. Switching Characteristics (Note)

#### (Unless otherwise specified, Ta = - 40 to 110 °C, $V_{CC2}$ - $V_{EE}$ = 15 to 30 V, $V_E$ - $V_{EE}$ = 0 V)

Characteristics Symbol			Test	Garadi	VEE - 15 to 5				11	
Characteristic		Symbol	Note	Circuit	Condition		Min	Тур.	Max	Unit
Propagation	L→H	t <sub>pLH</sub>				$I_F = 0 \rightarrow 10 \text{ mA}$	100	167	250	
delay time	H→L	t <sub>pHL</sub>	Note 1			$I_F = 10 \rightarrow 0 \text{ mA}$	100	170	250	
Pulse width distort	tion	t <sub>pHL</sub> -t <sub>pLH</sub>			$R_g = 10 \Omega,$ $C_g = 10 nF,$		-	3	50	
Propagation delay (device to device)		t <sub>psk</sub>	Note 1 Note 2	13.1. 11	$V_{CC2} = 30 \text{ V}$ f = 10 kHz,	I <sub>F</sub> = 10 ↔ 0 mA	-150	-	150	ns
Output rise time (10-90 %)		t <sub>r</sub>	Note 1		duty = 50 %	$I_F = 0 \rightarrow 10 \text{ mA}$	-	57	ı	
Output fall time (90-10 %)		t <sub>f</sub>	Note 1			$I_F=10 \rightarrow 0 \text{ mA}$	-	56	ı	
DESAT Sense to 9 V <sub>OUT</sub> Delay	0%	t <sub>DESAT</sub> (90%)					_	147	500	ns
DESAT Sense to 1 V <sub>OUT</sub> Delay	0%	t <sub>DESAT(10%)</sub>			$C_{DESAT} = 100 \text{ pF}$ $R_q = 10 \Omega$ ,		-	2	3	μς
DESAT leading edeblanking time	ge	t <sub>DESAT(LEB)</sub>			$C_g = 10 \text{ nF},$ $V_{CC2} = 30 \text{ V}$		-	1.27	ı	μS
DESAT filter time		t <sub>DESAT</sub> (FILTER)			VCC2 - 30 V		-	95	ı	
DESAT Sense to D Low Propagation [	-	t <sub>DESAT(LOW)</sub>					-	172	-	ns
DESAT Sense to L Level FAULT Signa		t		13.1. 12	$C_{DESAT} = 100 \text{ pF},$ $R_g = 10 \Omega,$ $C_q = 10 \text{ nF},$	$C_F = Open,$ $R_F = 2.1 \text{ k}\Omega$	-	343	500	ns
Delay	ai	t <sub>DESAT</sub> (FAULT)			$V_{CC2} = 30 \text{ V},$ $V_{CC1} = 5 \text{ V}$	$C_F = 1 \text{ nF},$ $R_F = 2.1 \text{ k}\Omega$	_	644	_	115
DESAT Input Mute	9	t <sub>DESAT(MUTE)</sub>					5	-	ı	
RESET to High Lev	/el				$C_{DESAT} = 100 \text{ pF},$ $R_g = 10 \Omega,$	$V_{CC1} = 5.5 \text{ V},$ $R_F = 2.1 \text{ k}\Omega$	0.1	0.63	2.5	μs
FAULT Signal Dela	ıy	<sup>t</sup> RESET(FAULT)			$C_g = 10 \text{ nF},$ $V_{CC2} = 30 \text{ V}$	$V_{CC1} = 3.3 \text{ V},$ $R_F = 2.1 \text{ k}\Omega$	0.1	0.65	2.5	
Output High Level Common Mode		CM	Note 3	13.1. 13,	Ta = 25 ℃ ,	$I_F = 10 \text{ mA},$ $C_F = 15 \text{ pF}$	±25	±40	_	
Transient Immuni	ty	CM <sub>H</sub>	NOTE 3	13.1. 14,	$V_{CM} = 1500 V_{P-P},$ $V_{CC2} = 30 V,$	$I_F = 10 \text{ mA},$ $C_F = 1 \text{ nF}$	±50	±100	_	kV/µs
Output Low Level Common Mode		CML	Note 4	13.1. 15, 13.1.	$R_F = 2.1 \text{ k}\Omega,$ $R_g = 10 \Omega,$	$V_F = 0 V$ , $C_F = 15 pF$	±25	±40		κν/μ5
Transient Immuni	ty	CitiL	NOIE 4	16	$C_g = 10 \text{ nF}$	$V_F = 0 V,$ $C_F = 1 nF$	±50	±100	_	

Note: All typical values are at  $T_a = 25$  °C. CF is approximately 15 pF which includes probe and stray wiring capacitance.

Note 1: Input signal: f = 10 kHz, duty = 50 %, tr = tf = 5 ns or less

Note 2: The propagation delay skew,  $t_{psk}$ , is equal to the magnitude of the worst-case difference in  $t_{phl}$  and/or  $t_{plh}$  that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

Note 3: Common mode transient immunity in the high state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in the high state ( $V_{OUT} > 23 \text{ V}$ ,  $V_{FAULT} > 3 \text{ V}$ ).

Note 4: Common mode transient immunity in the low state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in a low state ( $V_{OUT} < 1 \text{ V}$ ,  $V_{FAULT} < 2 \text{ V}$ ).



### 12. Application Information

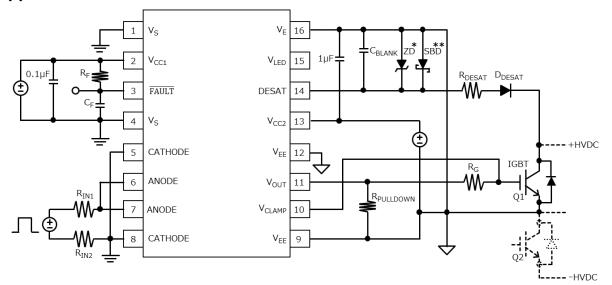


Fig 12.1 Recommended application circuit with positive gate drive, desaturation detection and active Miller Clamp

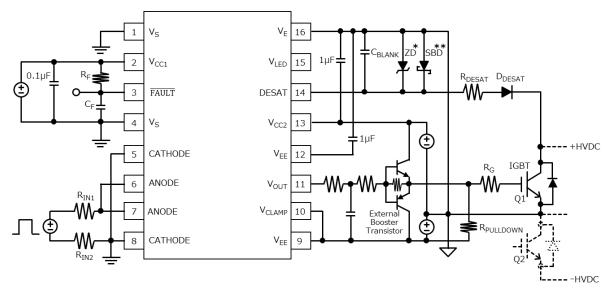


Fig 12.2 Recommended application circuit with negative gate drive, external booster transistors and desaturation detection

Note : Bypass capacitors (1  $\mu$ F) must be connected between pin 13 ( $V_{CC2}$ ) and 16 ( $V_E$ ) to stabilize the operation of the high gain linear amplifier. When  $V_E - V_{EE} > 0$  V (with negative gate drive), another bypass capacitor (1  $\mu$ F) must be connected between pin 9 or 12 ( $V_{EE}$ ) and 16 ( $V_E$ ). Failure to provide the bypassing may impair the switching property. The total lead length between each capacitor and the coupler should not exceed 1 cm.

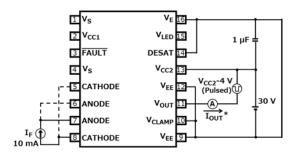
Refer to the connection of pin 14 and pin 16 for a desaturation detection function. The desaturation diode D<sub>DESAT</sub> 600V / 1200V fast recovery type and capacitor C<sub>BLANK</sub> are external components required for fault detection circuits. Also, select a resistance R<sub>DESAT</sub> of 500 ohms or more for protection of DESAT pin 14. For details, refer to the application note "Smart Gate Driver Coupler Tips for Designing DESAT Detection Circuits".

- : Zener diode for DESAT pin protection. CUZ8V2 is recommended.
- : Schottky diode for DESAT false detection prevention. CUS05F30 is recommended.



#### 13. Reference Drawings

#### 13.1. Test Circuits



\* : The direction of the arrow indicates the actual current direction.

Fig. 13.1.1 IOPH Test Circuit

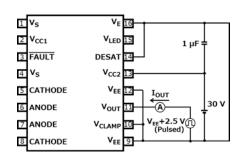
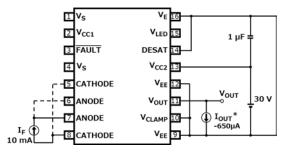


Fig. 13.1.2 IOPL Test Circuit



\* : The direction of the arrow indicates the actual current direction.

Fig. 13.1.3 V<sub>OH</sub> Test Circuit

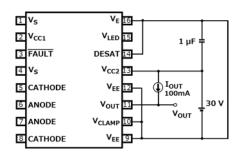
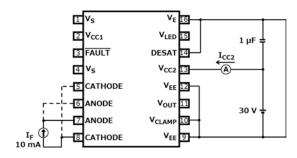


Fig. 13.1.4 V<sub>OL</sub> Test Circuit





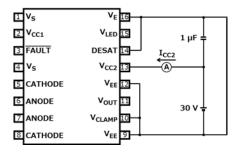
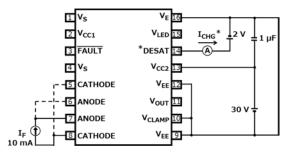


Fig. 13.1.6 I<sub>CC2L</sub> Test Circuit





\* : It operates as a constant current circuit. The direction of the arrow indicates the actual current direction.

Fig. 13.1.7 I<sub>CHG</sub> Test Circuit

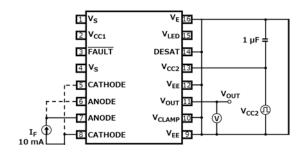
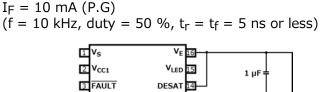
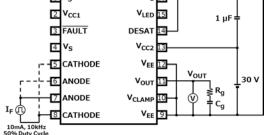


Fig. 13.1.9 V<sub>UVLO</sub> Test Circuit





P.G: Pulse Generator

 $t_{\text{pLH}}, t_{\text{pHL}}, t_{\text{r}}, t_{\text{f}}, |t_{\text{pHL}}-t_{\text{pLH}}|$ Test Circuit Fig 13.1.11

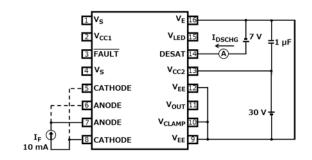


Fig. 13.1.8 I<sub>DSCHG</sub> Test Circuit

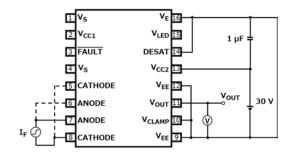
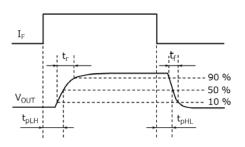
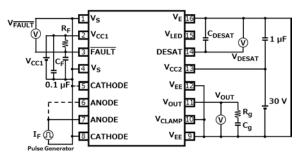


Fig. 13.1.10 I<sub>FLH</sub> Test Circuit

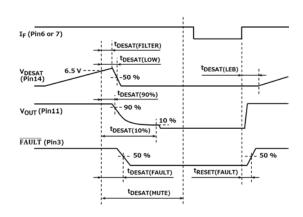


 $I_F$  = 10 mA (P.G) (f = 10 kHz, duty = 50 %,  $t_r$  =  $t_f$  = 5 ns or less)



P.G: Pulse Generator

Fig 13.1.12  $t_{DESAT(90\%)}$ ,  $t_{DESAT(10\%)}$ ,  $t_{DESAT(FAULT)}$ ,  $t_{DESAT(MUTE)}$ ,  $t_{RESET(FAULT)}$  Test Circuit



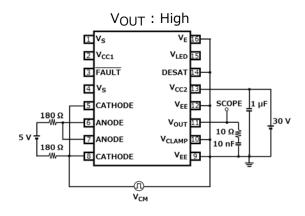


Fig 13.1.13 CMTI refer to V<sub>E</sub> Test Circuit (LED1 on)

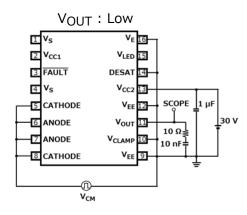


Fig 13.1.14 CMTI refer to V<sub>E</sub> Test Circuit (LED1 off)

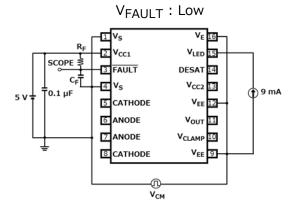


Fig 13.1.15 CMTI refer to V<sub>S</sub> Test Circuit (LED2 on)

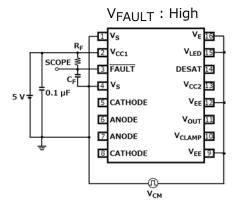


Fig 13.1.16 CMTI refer to V<sub>S</sub> Test Circuit (LED2 off)



#### 13.2. Timing Chart

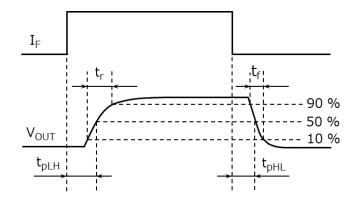


Fig 13.2.1 V<sub>OUT</sub> propagation delay waveforms

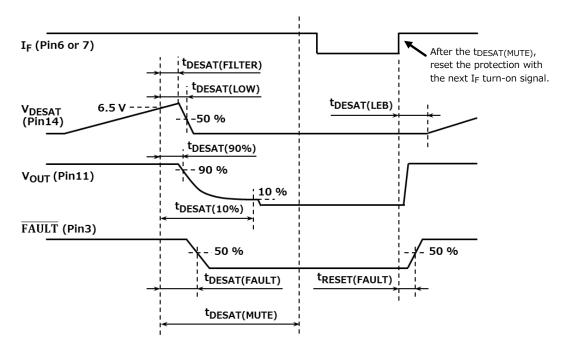


Fig 13.2.2 DESAT fault state timing diagram

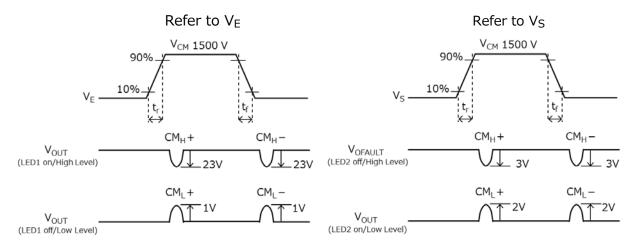


Fig 13.2.3 CMTI waveforms

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### 13.3. Characteristics Curves (Note)

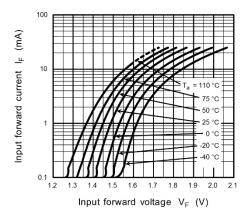


Fig 13.3.1 I<sub>F</sub> - V<sub>F</sub>

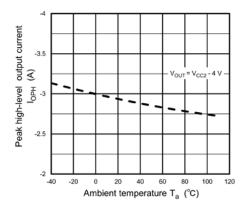


Fig 13.3.3  $I_{OPH}$  -  $T_a$ 

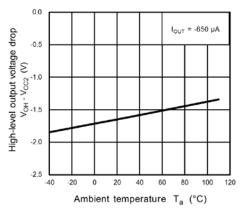


Fig 13.3.5 ( $V_{OH} - V_{CC2}$ ) -  $T_a$ 

13

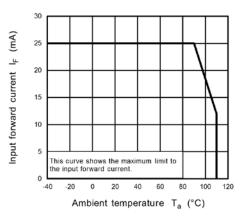


Fig 13.3.2 I<sub>F</sub> - T<sub>a</sub>

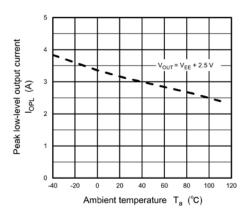


Fig 13.3.4  $I_{OPL}$  -  $T_a$ 

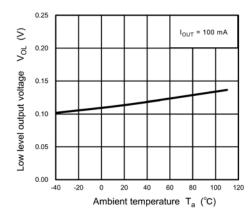


Fig 13.3.6  $V_{OL}$  -  $T_a$ 



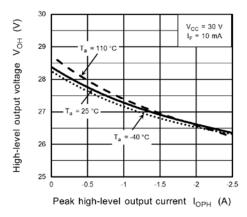


Fig 13.3.7  $V_{OH}$  -  $I_{OPH}$ 

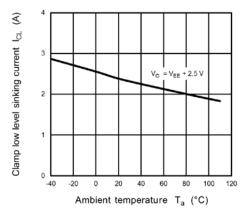


Fig 13.3.9  $I_{CL} - T_a$ 

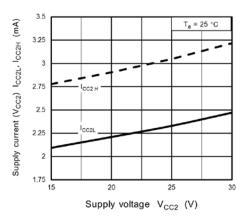


Fig 13.3.11 I<sub>CC2</sub> - V<sub>CC2</sub>

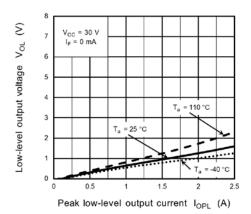
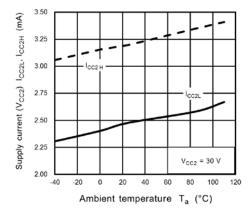


Fig 13.3.8  $V_{OL}$  -  $I_{OPL}$ 



 $Fig~13.3.10 \quad I_{CC2}-T_a$ 

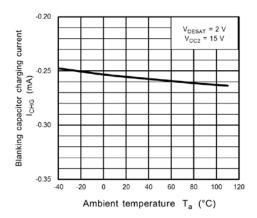


Fig 13.3.12  $I_{CHG}$  -  $T_a$ 



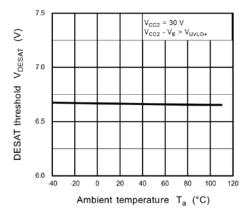


Fig 13.3.13  $V_{DESAT}$  -  $T_a$ 

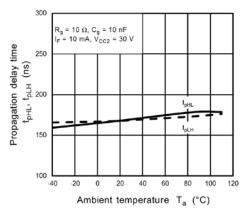


Fig 13.3.15  $t_{pLH}$ ,  $t_{pHL}$  -  $T_a$ 

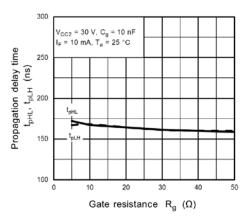


Fig 13.3.17  $t_{pLH}$ ,  $t_{pHL}$  -  $R_g$ 

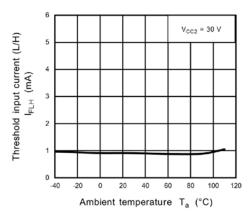


Fig 13.3.14 I<sub>FLH</sub> - T<sub>a</sub>

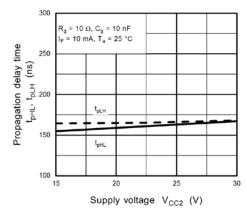


Fig 13.3.16  $t_{pLH}$ ,  $t_{pHL}$  -  $V_{CC2}$ 

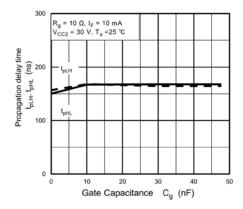


Fig 13.3.18  $t_{pLH}$ ,  $t_{pHL}$  -  $C_g$ 



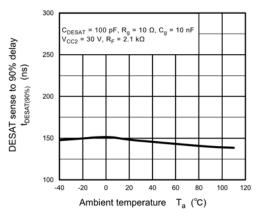
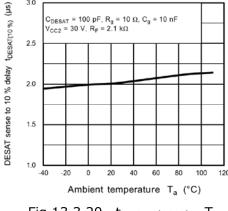


Fig 13.3.19  $t_{DESAT(90\%)}$  -  $T_a$ 



3.0

Fig 13.3.20  $t_{DESAT(10\%)}$  -  $T_a$ 

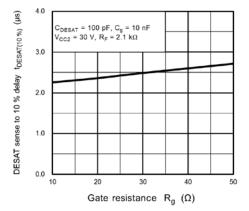


Fig 13.3.21  $t_{DESAT(10\%)} - R_g$ 

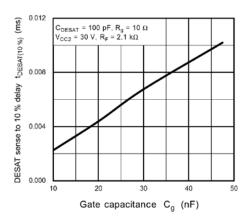


Fig 13.3.22 t<sub>DESAT(10%)</sub> - C<sub>q</sub>

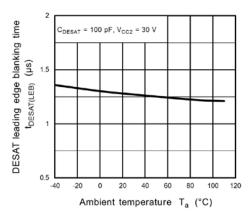


Fig 13.3.23  $t_{DESAT(LEB)}$  -  $T_a$ 

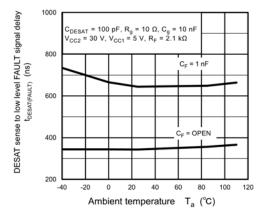


Fig 13.3.24  $t_{DESAT(FAULT)}$  -  $T_a$ 



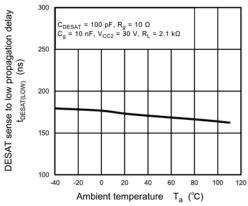


Fig 13.3.25 t<sub>DESAT(LOW)</sub> - T<sub>a</sub>

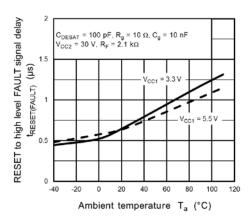


Fig 13.3.26  $t_{RESET(FAULT)}$  -  $T_a$ 

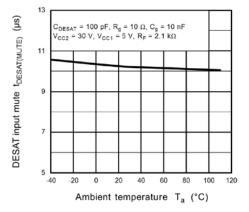


Fig 13.3.27  $t_{DESAT(MUTE)}$  -  $T_a$ 

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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#### 14. Soldering and Storage

#### 14.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

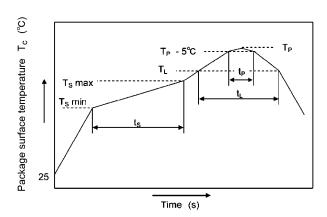
· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	S
Ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )			3	°C/s
Liquidus temperature	T <sub>L</sub>	217		ŷ
Time above T <sub>L</sub>	t∟	60	150	s
Peak temperature	T <sub>P</sub>		260	ů
Time during which $T_c$ is between $(T_P - 5)$ and $T_P$	t <sub>P</sub>		30	s
Ramp-down rate $(T_P \text{ to } T_L)$			6	°C/s

#### An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

· When using soldering flow

Preheat the device at a temperature of 150℃ (package surface temperature) for 60 to 120 seconds. Mounting condition of 260℃ within 10 seconds is recommended.

Flow soldering must be performed once.

· When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260℃ or within 3 seconds not exceeding 350℃.

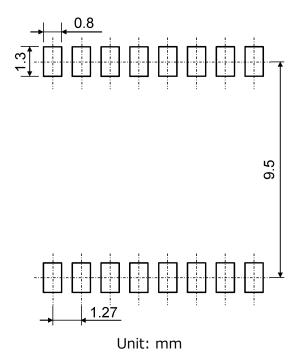
Heating by soldering iron must be done only once per lead.

#### 14.2. Precautions for General Storage

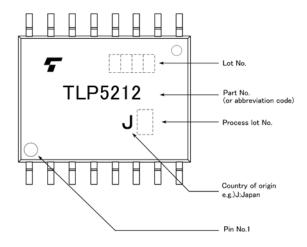
- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- · Follow the precautions printed on the packing label of the device for transportation and storage.
- · Keep the storage location temperature and humidity within a range of 5℃ to 35℃ and 45 % to 75 %, respectively.
- · Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- · Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- · Do not allow loads to be applied directly to devices while they are in storage.
- · If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.



## 15. Land Pattern Dimensions (for reference only)



### 16. Marking





### 17. EN 60747-5-5 Option (D4) Specification

• Part number: TLP5212 (Note 1)

• The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN 60747.

Example: TLP5212(D4-TP,E

D4: EN 60747 option

TP: Tape type

E: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP5212(D4-TP,E  $\rightarrow$  TLP5212

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

	Description	Symbol	Rating	Unit
Application classification				
for rated mains volta for rated mains volta			I-IV I-III	_
Climatic classification			40 / 110 / 21	_
Pollution degree			2	_
Maximum operating insul	ation voltage	VIORM	1230	Vpea
Input to output test voltage Vpr = 1.6 × VIORM, to tp = 10 s, partial disc	ype and sample test	Vpr	1970	Vpea
Input to output test voltage Vpr = 1.875 × VIORM tp = 1 s, partial disch	I, 100 % production test	Vpr	2310	Vpea
Highest permissible over (transient overvoltag	•	VTR	8000	Vpea
, ,	,	Isi Pso Ts	400 1200 175	mA mW °C
Insulation resistance	VIO = 500 V, T <sub>a</sub> = 25 °C VIO = 500 V, T <sub>a</sub> = 100 °C VIO = 500 V, T <sub>a</sub> = T <sub>s</sub>	Rsi	≥ 10 <sup>12</sup> ≥ 10 <sup>11</sup> ≥ 10 <sup>9</sup>	Ω

Fig 17.1 EN 60747 Insulation Characteristics



Minimum creepage distance	Cr	8.0 mm
Minimum clearance	CI	8.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Fig 17.2 Insulation Related Specifications (Note)

Please contact your Toshiba sales representative for details on environmental information such as the Note: product's RoHS compatibility.



Fig 17.3 Marking on Packing for EN 60747

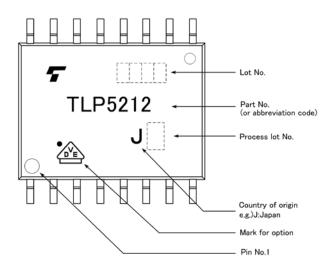


Fig 17.4 Marking Example (Note)

The above marking is applied to the photo couplers that have been qualified according to option (D4) Note: of EN 60747.

TLP5212



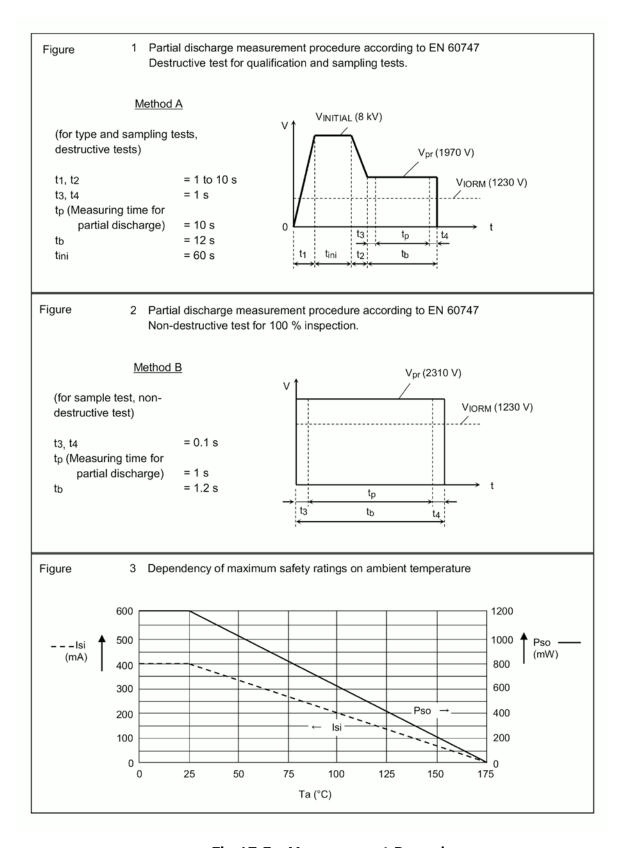


Fig 17.5 Measurement Procedure



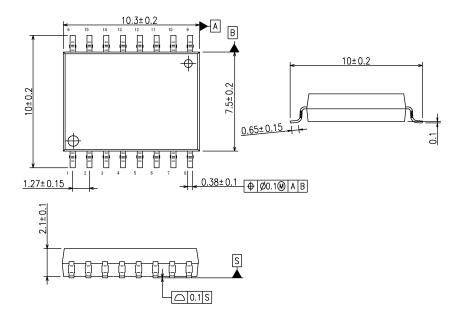
## 18. Ordering Information (Example of Item Name)

Item Name	VDE Option	Packing (MOQ)
TLP5212(E		Magazine (50 pcs)
TLP5212(TP,E		Tape and reel (1500 pcs)
TLP5212(D4,E	EN 60747-5-5	Magazine (50 pcs)
TLP5212(D4-TP,E	EN 60747-5-5	Tape and reel (1500 pcs)



## **Package Dimensions**

Unit: mm



Weight: 0.364 g (typ.)

Package Name(s)

TOSHIBA: 11-10M1



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